



南亞 高頻高速銅箔簡介

2023





南亞高頻高速用銅箔

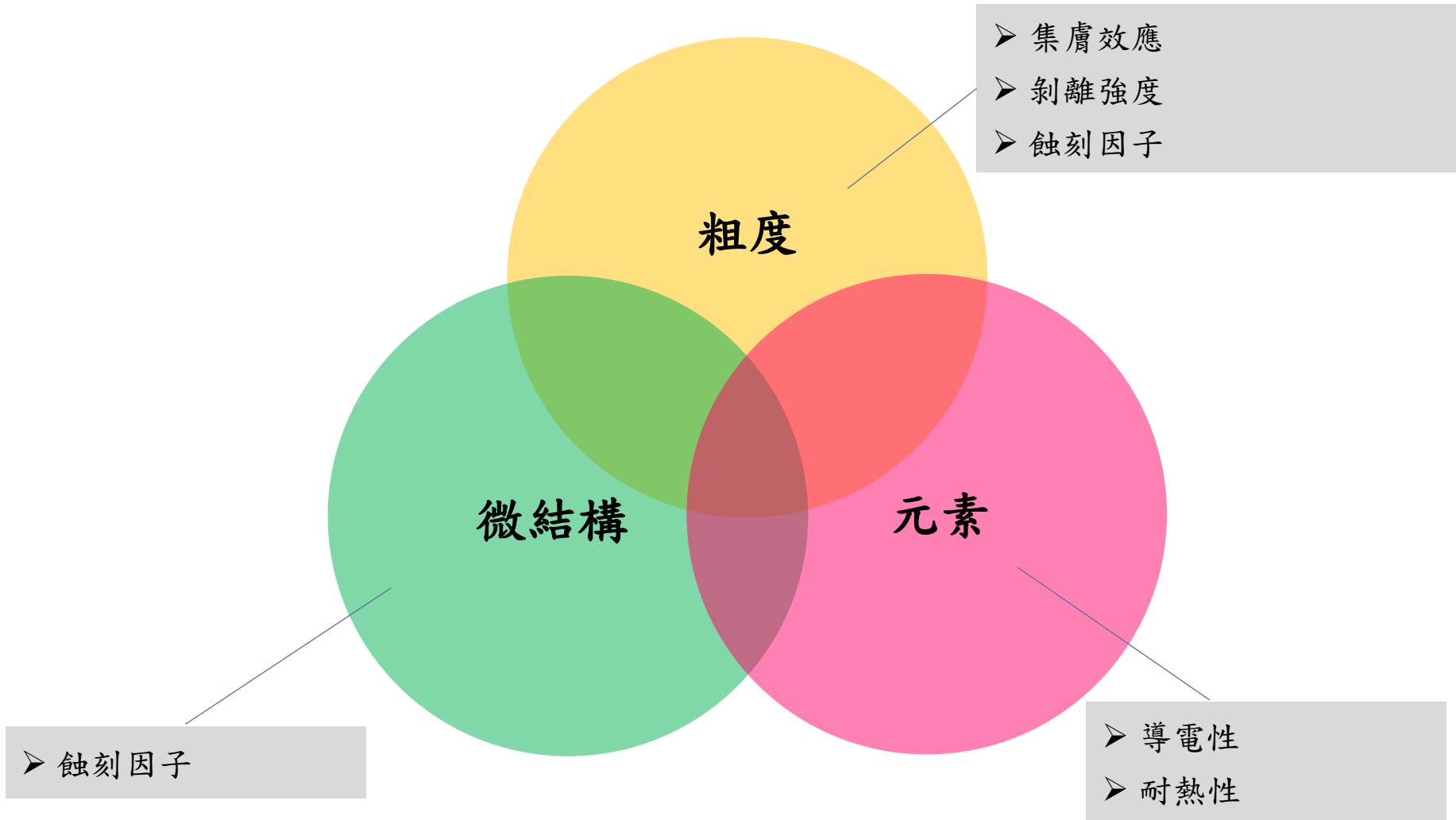
Grade		Product	Laminated Side				Status
			Contacting Roughness (μm)		Optical Roughness (μm)		
			Ra	Rz	Sa	Sz	
RTF	RTF	TLCHP	0.25	2.0	0.42	4.0	●
	RTF2	H1 / H1V	0.20	1.5	0.20	2.2	●
	RTF3	H1A	0.18	1.2	0.15	1.8	●
HVLP	HVLP	TLC-V2	0.25	2.1	0.35	3.3	●
	HVLP2	TLC-V1	0.22	1.5	0.27	2.7	●
	HVLP3	V1A	0.19	1.2	0.22	1.8	●
	HVLP4	VHA	0.16	1.0	0.20	1.5	⊗
PTFE	RTF	HW2	0.27	2.2	0.45	4.5	●
		HW1	0.25	1.7	0.32	3.5	●
	HVLP	VW	0.20	1.3	0.25	2.0	⊗

厚度規格: 12~70 μm

●: 量產品
⊗: 開發中



高頻高速PCB用銅箔設計

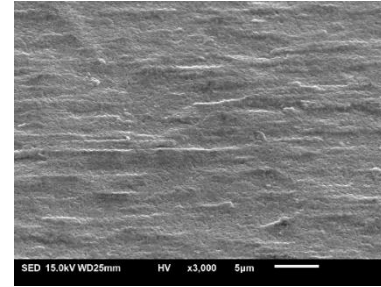
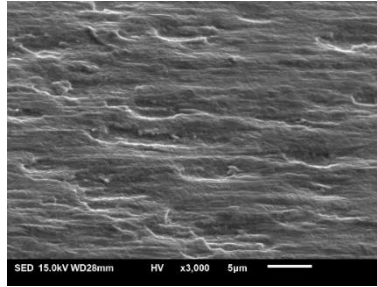




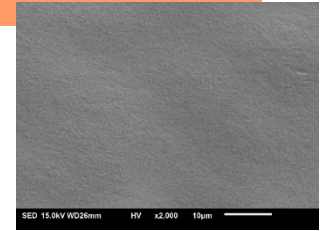
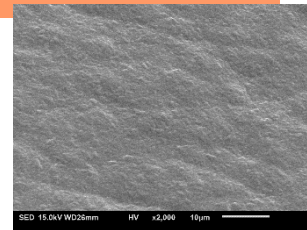
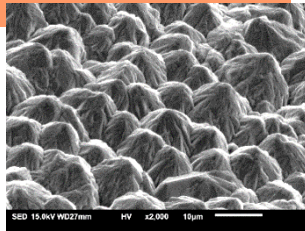
生箔工藝

降低粗度

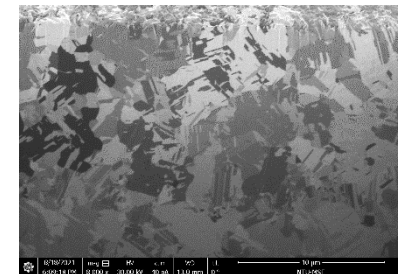
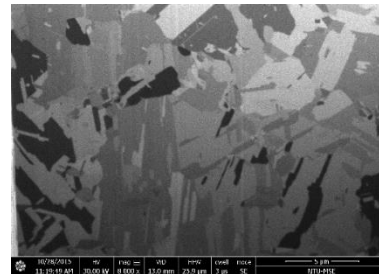
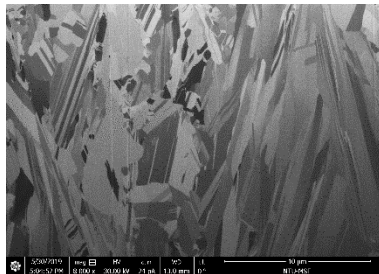
Shiny Side
(drum polish)



Matte Side

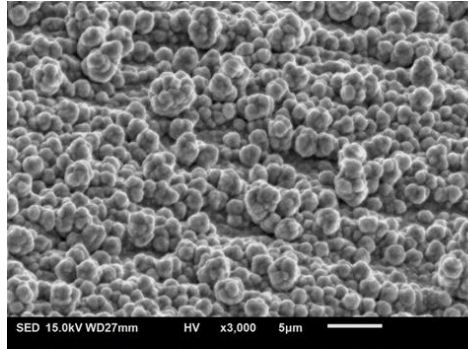


Microstructure

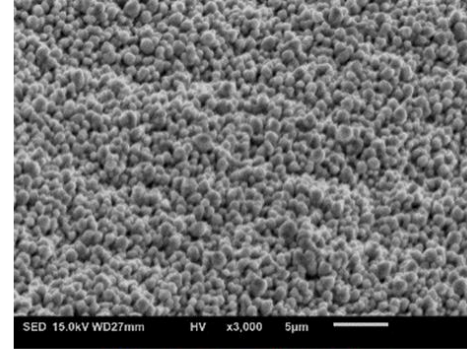




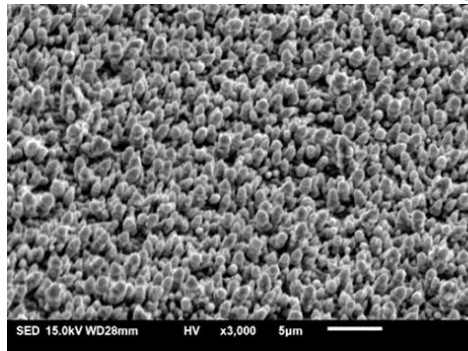
銅瘤設計



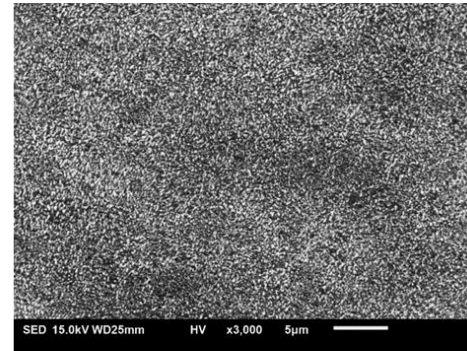
Traditional Spheroidal Type



Fine Spheroidal Type



Ellipse Type



Moss or Lichen Type

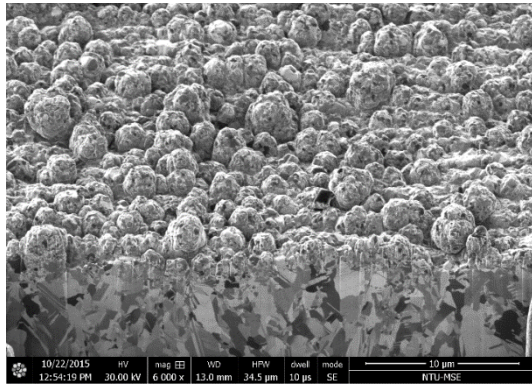
- 由先進粗化技術控制表面粗度、銅瘤型態與晶粒尺寸，減少訊號損耗。
- 球狀瘤狀物 ⇒ 細晶粒 ⇒ 絨毛狀



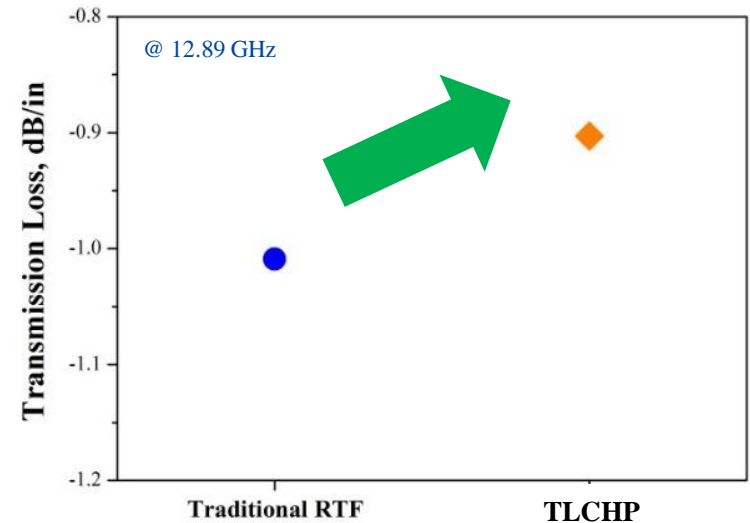
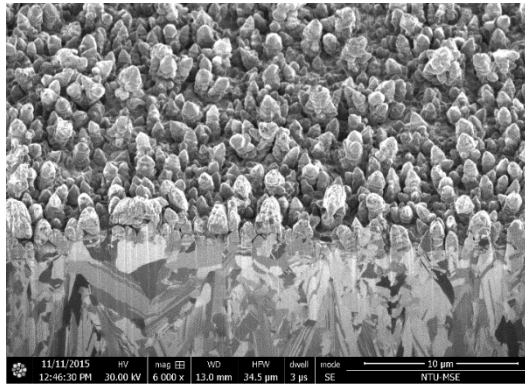
Low Roughness RTF – TLCHP

- 反轉處理銅箔
- $Rz \leq 2.5\mu\text{m}$
- 剝離強度 ≥ 5.0 lb/in (tested by NPG-170D)
- 橢圓銅瘤結構具有低粗度和高剝離強度的特性，適合低損耗PCB應用。

Traditional RTF



TLCHP



Loss improvement is about 12%

- 配合低粗度、高剝離強度及低信號損耗需求，使用了細晶粒粗化技術來改變銅瘤型態與降低銅瘤粒徑。
- 跟傳統RTF箔相比，TLCHP有更細緻的晶粒尺寸及更均一的結構，因此具有優良的訊號完整性。



Very Low Roughness RTF2 – H1

特徵

- $Rz \leq 1.5\mu m$
- 良好的插入損失
- 優異的尺寸安定性

應用

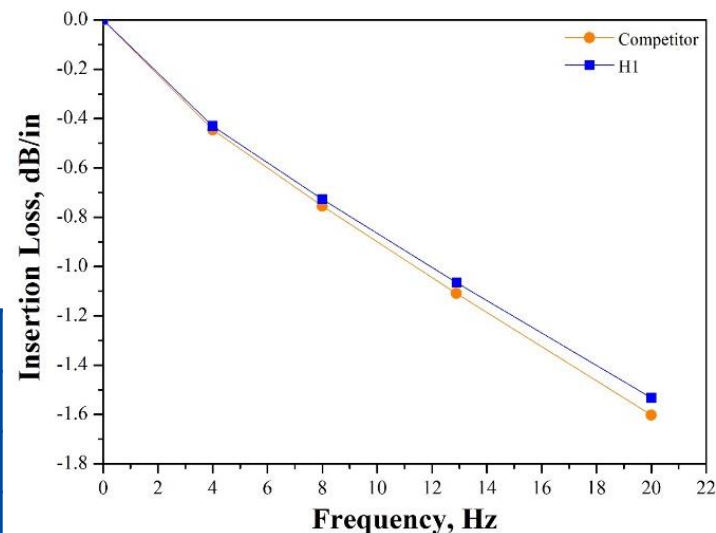
高端伺服器/路由器
光網絡/ Switch

Material: NPG-170D

PCB: 3 LB Stackup

4mil core(3313*1)+3313 PP*1

Measurement: Delta-L



➤ H1 訊號完整性優於他社銅箔。

Typical Properties

Product		H1	Competitor
Area weight (g/m ²)		283	285
Contacting roughness Ra / Rz (μm)	Resist side	0.74 / 4.7	0.88 / 5.2
	Laminated side	0.22 / 1.3	0.24 / 1.6
Non-contacting roughness (μm)	Sa	0.26	0.34
	Sq	0.32	0.43
	Sz	2.6	3.3
Peel strength(lb/in)	NPG-170D	4.5	4.6
Peel loss after soaked in 12% HCl for 1 hr (%)		3.0	3.5
Percentage of Loss after being heated 121°C 2hr (%)		5.0	35.5



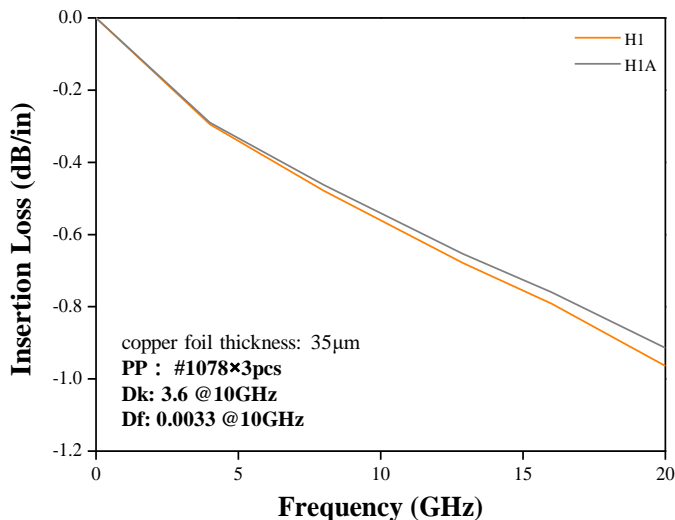
Very Low Roughness RTF3 – H1A

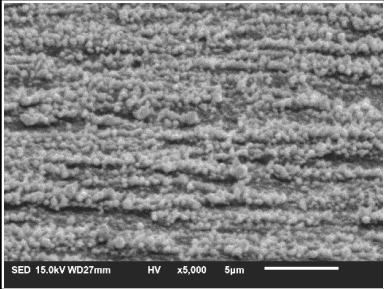
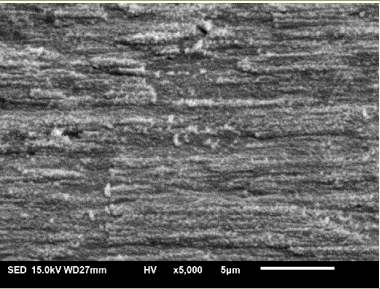
特徵

- $Rz \leq 1.3\mu\text{m}$
- 良好抗熱性
- 優良的訊號傳遞特性
- 優異的尺寸安定性

應用

高端伺服器/路由器
光網絡/Switch



品名		RTF2等級	RTF3等級
		H1	H1A
粗度 Ra / Rz (μm)	阻劑面	0.77 / 4.9	0.78 / 4.8
	壓合面	0.22 / 1.3	0.18 / 1.0
光學式粗度Sa/ Sz (μm)		0.26 / 2.6	0.20 / 1.7
SEM	壓合面		
剝離強度 (lb/in)		4.3	4.0
耐熱 ($^{\circ}\text{C}$) (測試時間 60分)		285	295

➤ H1A的銅瘤較細緻、粗度較低，故H1A高頻電性優於H1。



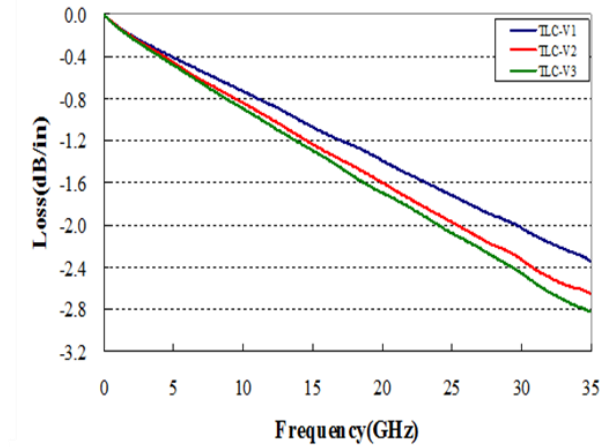
Very Low Roughness HVLP2 – V1

Material: NPG-170D

PCB: 3 LB Stackup

4mil core(3313*1)+3313 PP*1

Measurement: Delta-L



Product		TLC-V3	TLC-V2	TLC-V1
schematic diagram				
Nodule		Spheroidal 1.4 μm	Fine spheroidal 1.2 μm	Moss or Lichen 0.4 μm
Roughness, Ra/Rz (μm)	Resist side	0.20 / 1.3	0.23 / 1.3	0.18 / 1.1
	Laminated Side	0.54 / 3.5	0.27 / 2.2	0.20 / 1.3
Optical Roughness (Laminated Side)	Sa / Sq / Sz	0.74 / 0.91 / 5.96	0.41 / 0.39 / 3.43	0.27 / 0.33 / 2.51
SEM	Laminated Side			
Peel Strength (lb/in)	NPG-170D	5.2	4.9	4.5

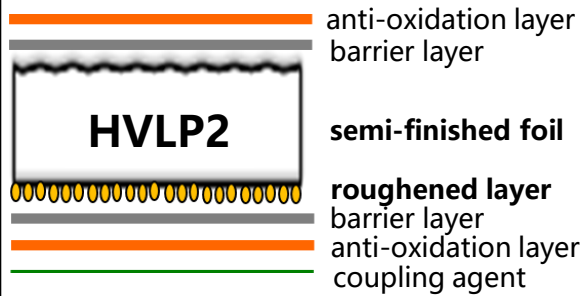
➤ 粗化技術調整壓合面的銅瘤型態與尺寸，降低銅箔粗糙度，有效提升高頻訊號完整性。



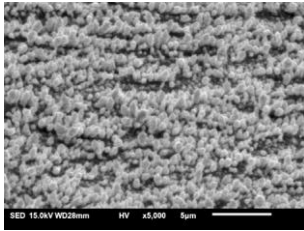
Very Low Roughness HVLP3 / HVLP4 – V1A / VHA

HVLP2 type

V1 copper foil

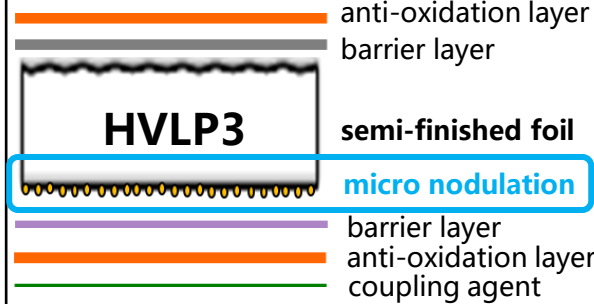


Rz: 1.5 μm
Sz: 3.2 μm

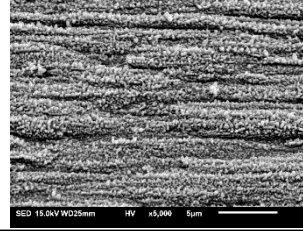


HVLP3 type

V1A copper foil



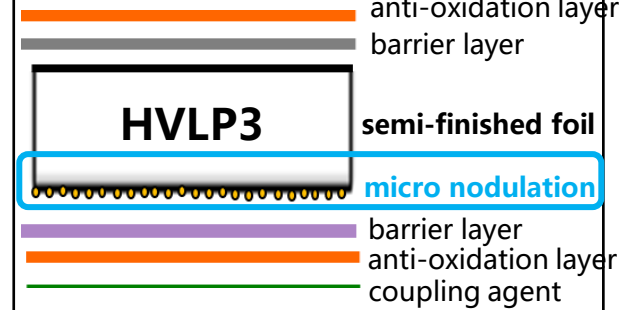
Rz: 1.0 μm
Sz: 2.0 μm



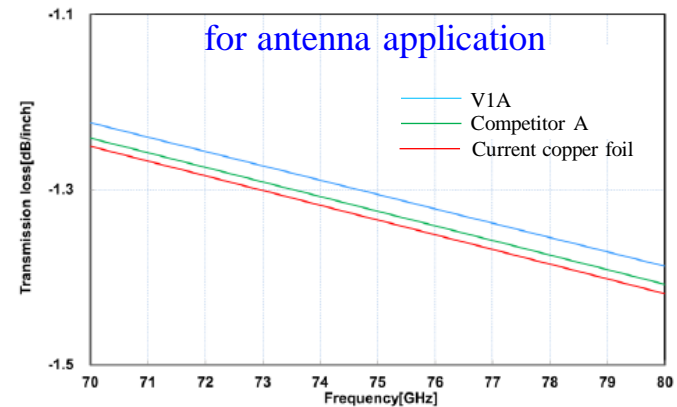
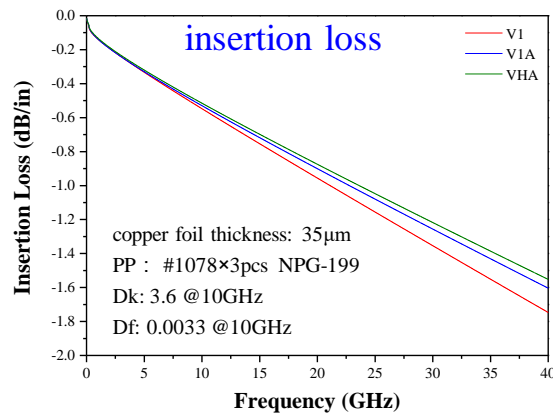
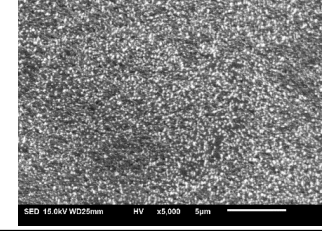
HVLP4 type

under development

VHA copper foil



Rz: 0.8 μm
Sz: 1.6 μm



➤ 南亞HVLP3及HVLP4等級銅箔，分別為V1A及VHA，都具有良好的訊號完整性。



研發藍圖

最終需求	銅箔開發	~ 2022	2023	2024	2025
<ul style="list-style-type: none">•Low Df•Low Dk•Low CTE	<ul style="list-style-type: none">•超低粗度•優良訊號完整性•高剝離強度•良好耐熱性•良好剛性	<ul style="list-style-type: none">•HVLP2 V1、V1V Rz ≤ 1.5 μm•RTF2 H1、H1V Rz ≤ 1.5 μm•For PTFE HW1、HW2 Rz ≤ 2.5 μm	<ul style="list-style-type: none">•HVLP3 V1A Rz ≤ 1.0 μm•RTF3 H1A Rz ≤ 1.0 μm	<ul style="list-style-type: none">•HVLP4 VHA Rz ≤ 0.8 μm•For PTFE VW1 Rz ≤ 1.5 μm	<ul style="list-style-type: none">•Profile-free Rz ≤ 0.5 μm Sz ≤ 1.0 μm



Thank you

<http://www.npc.com.tw>